

AMENDMENTS TO THE SPECIFICATION

Please replace paragraph [0027] with the following amended paragraph:

[0027] The tertiary alkyl group mentioned above is exemplified by those having three chain-like alkyl groups bonded to the tertiary carbon atom such as tert-butyl and tert-amyl groups and those alkyl-substituted monocyclic or polycyclic hydrocarbon groups of which two of the alkyl groups bonded to the tertiary carbon atom jointly form a cyclic structure such as 1-methylcyclohexyl, 1-ethylcyclohexyl, 1-propylcyclohexyl, ~~2-methyladamantyl~~ 2-methyladamantyl, 2-ethyladamantyl and 2-propyladamantyl groups. The alkyl group in the above mentioned mono- or polycyclic hydrocarbon groups is preferably a lower alkyl group such as methyl, ethyl and propyl groups.

Please replace paragraph [0069] with the following amended paragraph:

[0069] A semiconductor silicon wafer was uniformly coated with this photoresist solution followed by drying to form a dried photoresist layer having a thickness of 0.7 μm which exhibited a rate of film thickness reduction of 0.03 nm/second in a 2.38% by weight aqueous solution of tetramethylammonium hydroxide at 23 °C. The results of the evaluation tests undertaken for this photoresist composition are shown in Table 1 below.

Table 1

	Photo-sensitivity, mJ/cm^2	Cross sectional profile of patterned resist layer	Pattern resolu- tion, μm	Number of defects
Example 1	30	A	0.18	5
Example 2	32	A	0.18	5
Comparative Example 1	30	A	0.17	1200
Comparative Example 2	34	A	$[[0,17]]$ <u>0.17</u>	1000